

NPN SILICON RF POWER TRANSISTOR

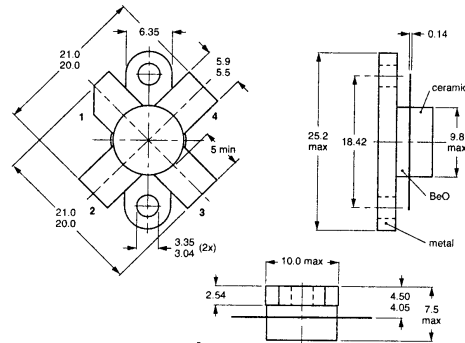
DESCRIPTION:

The **ASI MRF422** is Designed for 2.0 MHz to 30 MHz, 28 V High Power Linear Amplifier Applications. For h_{FE} Matched Pairs Order **ASI MRF422MP**.

MAXIMUM RATINGS

I	20 A
V	40 V
P_{DISS}	290 W @ $T_C = 25\text{ }^{\circ}\text{C}$
T_J	-65 $^{\circ}\text{C}$ to +150 $^{\circ}\text{C}$
T_{STG}	-65 $^{\circ}\text{C}$ to +150 $^{\circ}\text{C}$
θ_{JC}	0.6 $^{\circ}\text{C/W}$

PACKAGE STYLE .500 4L FLG



1 = COLLECTOR 3 = BASE
2 & 4 = EMITTER

CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200\text{ mA}$	35			V
BV_{CES}	$I_C = 100\text{ mA}$	85			V
BV_{CBO}	$I_C = 100\text{ mA}$	85			V
BV_{EBO}	$I_E = 10\text{ mA}$	3.0			V
I_{CES}	$V_{CE} = 28\text{ V}$			20	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 5.0\text{ A}$	10	30	120	---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$		420		pF
P_{out}	$V_{CE} = 28\text{ V}$ $f = 30\text{ MHz}$	150			W(PEP)
G_{PE}	$V_{CC} = 28\text{ V}$ $I_{CQ} = 150\text{ mA}$ $P_{out} = 150\text{ W (PEP)}$	10	13		dB
η	$I_{C(max)} = 6.7\text{ A}$ $f = 30\text{ MHz}$		45		%
IMD			-33		dB